SN74LVC1T45 可変電圧変換設定、3 ステート出力、1 ビット・デュアル電源バス・トランシーバ

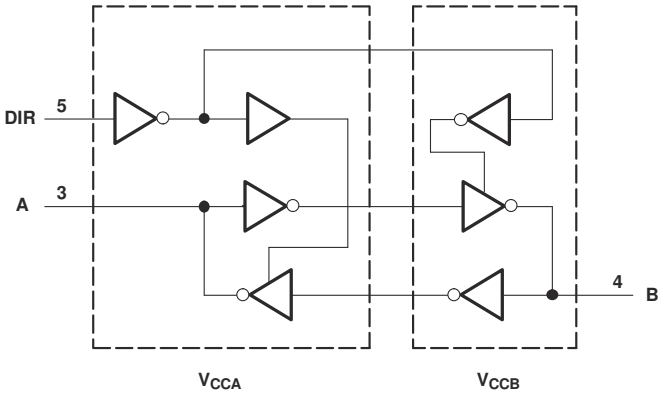
1 特長

- JESD 22 を超える ESD 保護
  - 2000V、人体モデル (A114-A)
  - 200V、マシン・モデル (A115-A)
  - 1000V、デバイス帯電モデル (C101)
- テキサス・インスツルメンツの NanoFree™ パッケージで供給
- 完全に構成可能なデュアル・レール設計により、1.65V～5.5V の電源電圧の全範囲にわたって各ポートが動作可能
- V_{CC} 絶縁機能：いずれかの V_{CC} 入力が GND レベルになると、両方のポートがハイ・インピーダンス状態に移行
- V_{CCA} を基準とする DIR 入力回路
- 低い消費電力、最大 I_{CC}：4μA
- 3.3V において ±24mA の出力駆動能力
- I_{off} により部分的パワーダウン・モードでの動作をサポート
- 最大データ・レート
  - 420Mbps (3.3V から 5V に変換)
  - 210Mbps (3.3V に変換)
  - 140Mbps (2.5V に変換)
  - 75Mbps (1.8V に変換)
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能

2 アプリケーション

- パーソナル・エレクトロニクス
- 産業用
- エンタープライズ
- テレコム

機能ブロック図



3 概要

この 1 ビット非反転バス・トランシーバは、設定可能な 2 本の独立した電源レールを使用します。A ポートは V_{CCA} に追従する設計で、V_{CCA} は 1.65V～5.5V の任意の電源電圧に対応できます。B ポートは V_{CCB} に追従する設計で、V_{CCB} は 1.65V～5.5V の任意の電源電圧に対応できます。このため、1.8V、2.5V、3.3V、5V の任意の電圧ノード間での自在な低電圧双方向変換が可能です。

SN74LVC1T45 は、2 つのデータ・バス間の非同期通信用に設計されています。方向制御 (DIR) 入力のロジック・レベルにより、B ポート出力と A ポート出力のどちらかがアクティブになります。本デバイスは、B ポート出力をアクティブにした場合、A バスから B バスにデータを送信し、A ポート出力をアクティブにした場合、B バスから A バスにデータを送信します。A ポートと B ポートの両方の入力回路は常にアクティブであるため、I_{CC} と I_{CCZ} が過剰に流れないようにロジック High または Low レベルを印加する必要があります。

SN74LVC1T45 は、DIR 入力が V_{CCA} によって給電されるように設計されています。このデバイスは、I_{off} を使用する部分的パワーダウン・アプリケーション用の動作が完全に規定されています。I_{off} 回路が出力をディセーブルにするため、電源切断時にデバイスに電流が逆流して損傷に至ることを回避できます。V_{CC} 絶縁機能は、いずれかの V_{CC} 入力が GND レベルになると、両方のポートがハイ・インピーダンス状態になるよう設計されています。

NanoFree パッケージ技術は IC パッケージの概念における主要なブレークスルーであり、ダイをパッケージとして使用します。

パッケージ情報

部品番号	パッケージ (1)	本体サイズ (公称)
SN74LVC1T45	DRL (SOT、6)	1.60mm × 1.20mm
	DBV (SOT-23、6)	2.90mm × 1.60mm
	DCK (SC70、6)	2.00mm × 1.25mm
	DPK (USON、6)	1.60mm × 1.60mm
	YZP (DSBGA、6)	1.39mm × 0.90mm

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。

英語版の TI 製品についての情報を翻訳したこの資料は、製品の概要を確認する目的で便宜的に提供しているものです。該当する正式な英語版の最新情報は、www.ti.com で閲覧でき、その内容が常に優先されます。TI では翻訳の正確性および妥当性につきましては一切保証いたしません。実際の設計などの前には、必ず最新版の英語版をご参照くださいますようお願いいたします。

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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision L (February 2017) to Revision M (November 2022) — **Page**

- 文書全体にわたって表、図、相互参照の採番方法を更新 ... 1
- Updated the thermals in the *Thermal Information* section ... 6
- Updated the *Switching Characterisitcs* sections: extended some minimum specifications for lower delays ... 8
- Updated the *I_{off} Supports Partial Power-Down Mode Operation* section ... 14
- Added the *Balanced High-Drive CMOS Push-Pull Outputs* and *V_{CC} Isolation* sections ... 14
- Updated the *Power Supply Recommendations* section ... 19

Changes from Revision K (December 2014) to Revision L (February 2017) — **Page**

- DPK (USON) パッケージの情報を追加 ... 1
- 「ドキュメントのサポート」セクション、「ドキュメントの更新通知を受け取る方法」セクション、「コミュニティ・リソース」セクションを追加 ... 1
- Added Junction temperature, T_J in *Absolute Maximum Ratings* ... 5

Changes from Revision J (December 2013) to Revision K (December 2014) — **Page**

- 「ピン構成および機能」セクション、「ESD 定格」表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクションを追加 ... 1

Changes from Revision I (December 2011) to Revision J (December 2013) — **Page**

- 新しいテキサス・インスツルメンツのデータシート・フォーマットにドキュメントを更新 - 仕様変更なし ... 1
- 注文情報を削除 ... 1
- ESD の警告を追加 ... 1

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5 Pin Configuration and Functions

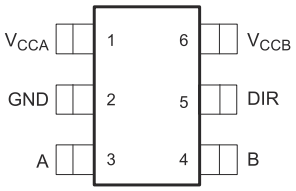

図 5-1. DBV Package, 6-Pin SOT-23 (Top View)

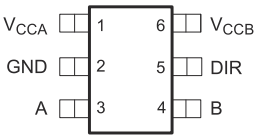

図 5-2. DCK Package, 6-Pin SC70 (Top View)

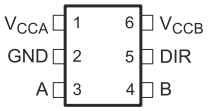

図 5-3. DRL Package, 6-Pin SOT (Top View)

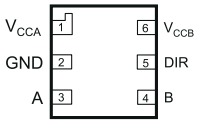

図 5-4. DPK Package, 6-Pin USON (Top View)

表 5-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	DBV, DCK, DRL, DPK		
V_{CCA}	1	P	SYSTEM-1 supply voltage (1.65 V to 5.5 V)
GND	2	G	Device GND
A	3	I/O	Output level depends on V_{CC1} voltage.
B	4	I/O	Input threshold value depends on V_{CC2} voltage.
DIR	5	I	GND (low level) determines B-port to A-port direction.
V_{CCB}	6	P	SYSTEM-2 supply voltage (1.65 V to 5.5 V)

(1) P = power, G = ground, I/O = input and output, I = input

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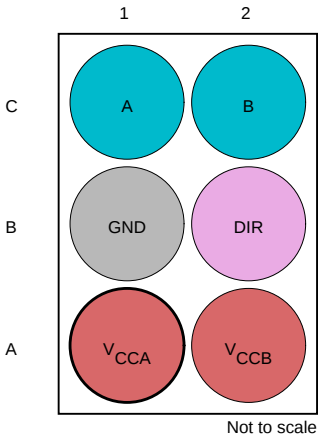

図 5-5. YZP Package, 6-Pin DSBGA (Bottom View)

Legend	
Power	Input
Input or Output	Ground

表 5-2. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NO.	NAME		
A1	V_{CCA}	P	SYSTEM-1 supply voltage (1.65 V to 5.5 V)
A2	V_{CCB}	P	SYSTEM-2 supply voltage (1.65 V to 5.5 V)
B1	GND	G	Device GND
B2	DIR	I	GND (low level) determines B-port to A-port direction.
C1	A	I/O	Output level depends on V_{CC1} voltage.
C2	B	I/O	Input threshold value depends on V_{CC2} voltage.

(1) P = power, G = ground, I/O = input and output, I = input

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CCA} V_{CCB}	Supply voltage		–0.5	6.5	V
V_I	Input voltage(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state(2) (3)	A port	–0.5	V_{CCA} + 0.5	V
		B port	–0.5	V_{CCB} + 0.5	
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(3) The value of V_{CC} is provided in the recommended operating conditions table.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	
		Machine Model	±200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See (1) (2) (3)

			V_{CCI}	V_{CCO}	MIN	MAX	UNIT
V_{CCA}	Supply voltage				1.65	5.5	V
V_{CCB}					1.65	5.5	
V_{IH}	High-level input voltage	Data inputs(4)	1.65 o 1.95 V		V_{CCI} × 0.65		V
			2.3 to 2.7 V		1.7		
			3 to 3.6 V		2		
			4.5 to 5.5 V		V_{CCI} × 0.7		
V_{IL}	Low-level input voltage	Data inputs(4)	1.65 o 1.95 V			V_{CCI} × 0.35	V
			2.3 to 2.7 V			0.7	
			3 to 3.6 V			0.8	
			4.5 to 5.5 V			V_{CCI} × 0.3	
V_{IH}	High-level input voltage	DIR (referenced to V_{CCA})(5)	1.65 to 1.95 V		V_{CCA} × 0.65		V
			2.3 to 2.7 V		1.7		
			3 to 3.6 V		2		
			4.5 to 5.5 V		V_{CCA} × 0.7		

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6.3 Recommended Operating Conditions (continued)

See (1) (2) (3)

			V_{CCI}	V_{CCO}	MIN	MAX	UNIT
V_{IL}	Low-level input voltage	DIR (referenced to V_{CCA})(5)	1.65 to 1.95 V			V_{CCA} × 0.35	V
			2.3 to 2.7 V			0.7	
			3 to 3.6 V			0.8	
			4.5 to 5.5 V			V_{CCA} × 0.3	
V_I	Input voltage				0	5.5	V
V_O	Output voltage				0	V_{CCO}	V
I_{OH}	High-level output current			1.65 to 1.95 V		–4	mA
				2.3 to 2.7 V		–8	
				3 to 3.6 V		–24	
				4.5 to 5.5 V		–32	
I_{OL}	Low-level output current			1.65 to 1.95 V		4	mA
				2.3 to 2.7 V		8	
				3 to 3.6 V		24	
				4.5 to 5.5 V		32	
Δt/Δv	Input transition rise or fall rate	Data inputs	1.65 to 1.95 V			20	ns/V
			2.3 to 2.7 V			20	
			3 to 3.6 V			10	
			4.5 to 5.5 V			5	
		Control inputs	1.65 to 5.5 V			5	
T_A	Operating free-air temperature				–40	85	°C

(1) V_{CCI} is the V_{CC} associated with the input port.
(2) V_{CCO} is the V_{CC} associated with the output port.
(3) All unused data inputs of the device must be held at V_{CCI} or GND to ensure proper device operation. See the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.
(4) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCI} × 0.7 V, V_{IL} max = V_{CCI} × 0.3 V.
(5) For V_{CCI} values not specified in the data sheet, V_{IH} min = V_{CCA} × 0.7 V, V_{IL} max = V_{CCA} × 0.3 V.

6.4 Thermal Information

THERMAL METRIC(1)		SN74LVC1T45					UNIT
		DBV (SOT-23)	DCK (SC70)	DPK (USON)	DRL (SOT)	YZP (DSBGA)	
		6 PINS					
$R_{\theta JA}$	Junction-to-ambient thermal resistance	215.1	210.9	278.3	223.7	131.0	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	136.5	139.2	133.4	88.7	1.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	96.6	72	174.1	58.4	22.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	71.5	54.9	23.4	5.9	5.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	96.3	71.7	173.5	58.1	22.6	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

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6.5 Electrical Characteristics

over recommended operating free-air temperature range, T_A = –40 to +85°C (unless otherwise noted)(1) (2)

PARAMETER		TEST CONDITIONS		V_{CCA}	V_{CCB}		MIN	TYP	MAX	UNIT
V_{OH}		I_{OH} = –100 µA	$V_I = V_{IH}$	1.65 to 4.5 V	1.65 to 4.5 V		V_{CCO} – 0.1			V
		I_{OH} = –4 mA		1.65 V	1.65 V		1.2			
		I_{OH} = –8 mA		2.3 V	2.3 V		1.9			
		I_{OH} = –24 mA		3 V	3 V		2.4			
		I_{OH} = –32 mA		4.5 V	4.5 V		3.8			
V_{OL}		I_{OL} = 100 µA	$V_I = V_{IL}$	1.65 to 4.5 V	1.65 to 4.5 V				0.1	V
		I_{OL} = 4 mA		1.65 V	1.65 V				0.45	
		I_{OL} = 8 mA		2.3 V	2.3 V				0.3	
		I_{OL} = 24 mA		3 V	3 V				0.55	
		I_{OL} = 32 mA		4.5 V	4.5 V				0.55	
I_I	DIR	$V_I = V_{CCA}$ or GND		1.65 to 5.5 V	1.65 to 5.5 V	T_A = 25 °C			±1	µA
						T_A = –40 to +85°C			±2	
I_{off}	A port	V_I or V_O = 0 to 5.5 V		0 V	0 to 5.5 V	T_A = 25 °C			±1	µA
						T_A = –40 to +85°C			±2	
	B port			0 to 5.5 V	0 V	T_A = 25 °C			±1	
						T_A = –40 to +85°C			±2	
I_{OZ}	A or B port	$V_O = V_{CCO}$ or GND		1.65 to 5.5 V	1.65 to 5.5 V	T_A = 25 °C			±1	µA
						T_A = –40 to +85°C			±2	
I_{CCA}		$V_I = V_{CCI}$ or GND, I_O = 0		1.65 to 5.5 V	1.65 to 5.5 V				3	µA
				5.5 V	0 V				2	
				0 V	5.5 V				–2	
I_{CCB}		$V_I = V_{CCI}$ or GND, I_O = 0		1.65 to 5.5 V	1.65 to 5.5 V				3	µA
				5.5 V	0 V				–2	
				0 V	5.5 V				2	
$I_{CCA} + I_{CCB}$ (see 表 8-1)		$V_I = V_{CCI}$ or GND, I_O = 0		1.65 to 5.5 V	1.65 to 5.5 V				4	µA
ΔI_{CCA}	A port	A port at V_{CCA} – 0.6 V, DIR at V_{CCA}, B port = open		3 to 5.5 V	3 to 5.5 V				50	µA
	DIR	DIR at V_{CCA} – 0.6 V, B port = open, A port at V_{CCA} or GND							50	
ΔI_{CCB}	B port	B port at V_{CCB} – 0.6 V, DIR at GND, A port = open		3 to 5.5 V	3 to 5.5 V				50	µA
C_i	DIR	$V_I = V_{CCA}$ or GND		3.3 V	3.3 V	T_A = 25 °C		2.5		pF
C_{io}	A or B port	$V_O = V_{CCA/B}$ or GND		3.3 V	3.3 V	T_A = 25 °C		6		pF

(1) V_{CCO} is the V_{CC} associated with the output port.
(2) V_{CCI} is the V_{CC} associated with the input port.

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6.6 Switching Characteristics (V_{CCA} = 1.8 V ± 0.15 V)

over recommended operating free-air temperature range, V_{CCA} = 1.8 V ± 0.15 V (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	3	17.7	2.2	10.3	1.7	8.3	1.4	7.2	ns
t_{PHL}			2.8	14.3	2.2	8.5	1.8	7.1	1.7	7	
t_{PLH}	B	A	3	17.7	2.3	16	2.1	15.5	1.9	15.1	ns
t_{PHL}			2.8	14.3	2.1	12.9	2	12.6	1.8	12.2	
t_{PHZ}	DIR	A	5.2	19.4	4.8	18.5	4.7	18.4	5.1	17.1	ns
t_{PLZ}			2.3	10.5	2.1	10.5	2.4	10.7	3.1	10.9	
t_{PHZ}	DIR	B	5.2	21.9	4.9	11.5	4.6	10.3	2.8	8.2	ns
t_{PLZ}			4.2	16	3.7	9.2	3.3	8.4	2.4	6.4	
t_{PZH} (1)	DIR	A		33.7		25.2		23.9		21.5	ns
t_{PZL} (1)				36.2		24.4		22.9		20.4	
t_{PZH} (1)	DIR	B		28.2		20.8		19		18.1	ns
t_{PZL} (1)				33.7		27		25.5		24.1	

(1) The enable time is a calculated value, derived using the formula shown in the *セクション 9.2.2.2.1* section.

6.7 Switching Characteristics (V_{CCA} = 2.5 V ± 0.2 V)

over recommended operating free-air temperature range, V_{CCA} = 2.5 V ± 0.2 V (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	2.3	16	1.5	8.5	1.3	6.4	1.1	5.1	ns
t_{PHL}			2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	
t_{PLH}	B	A	2.2	10.3	1.5	8.5	1.4	8	1	7.5	ns
t_{PHL}			2.2	8.5	1.4	7.5	1.3	7	0.9	6.2	
t_{PHZ}	DIR	A	3	8.1	3.1	8.1	2.8	8.1	3.2	8.1	ns
t_{PLZ}			1.3	5.9	1.3	5.9	1.3	5.9	1	5.8	
t_{PHZ}	DIR	B	5.2	23.7	4.1	11.4	3.9	10.2	2.4	7.1	ns
t_{PLZ}			3.9	18.9	3.2	9.6	2.8	8.4	1.8	5.3	
t_{PZH} (1)	DIR	A		29.2		18.1		16.4		12.8	ns
t_{PZL} (1)				32.2		18.9		17.2		13.3	
t_{PZH} (1)	DIR	B		21.9		14.4		12.3		10.9	ns
t_{PZL} (1)				21		15.6		13.5		12.7	

(1) The enable time is a calculated value, derived using the formula shown in the *セクション 9.2.2.2.1* section.

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6.8 Switching Characteristics (V_{CCA} = 3.3 V ± 0.3 V)

over recommended operating free-air temperature range, V_{CCA} = 3.3 V ± 0.3 V (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	2.1	15.5	1.4	8	0.7	5.8	0.7	4.4	ns
t_{PHL}			2	12.6	1.3	7	0.8	5	0.7	4	
t_{PLH}	B	A	1.7	8.3	1.3	6.4	0.7	5.8	0.6	5.4	ns
t_{PHL}			1.8	7.1	1.3	5.4	0.8	5	0.7	4.5	
t_{PHZ}	DIR	A	2.9	7.3	3	7.3	2.8	7.3	3.4	7.3	ns
t_{PLZ}			1.8	5.6	1.6	5.6	2.2	5.7	2.2	5.7	
t_{PHZ}	DIR	B	5.4	20.5	3.9	10.1	2.9	8.8	2.4	6.8	ns
t_{PLZ}			3.3	14.5	2.9	7.8	2.4	7.1	1.7	4.9	
t_{PZH} (1)	DIR	A		22.8		14.2		12.9		10.3	ns
t_{PZL} (1)				27.6		15.5		13.8		11.3	
t_{PZH} (1)	DIR	B		21.1		13.6		11.5		10.1	ns
t_{PZL} (1)				19.9		14.3		12.3		11.3	

(1) The enable time is a calculated value, derived using the formula shown in the *セクション 9.2.2.2.1* section.

6.9 Switching Characteristics (V_{CCA} = 5 V ±0.5 V)

over recommended operating free-air temperature range, V_{CCA} = 5 V ±0.5 V (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CCB} = 1.8 V ±0.15 V		V_{CCB} = 2.5 V ±0.2 V		V_{CCB} = 3.3 V ±0.3 V		V_{CCB} = 5 V ±0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	B	1.9	15.1	1	7.5	0.6	5.4	0.5	3.9	ns
t_{PHL}			1.8	12.2	0.9	6.2	0.7	4.5	0.5	3.5	
t_{PLH}	B	A	1.4	7.2	1	5.1	0.7	4.4	0.5	3.9	ns
t_{PHL}			1.7	7	0.9	4.6	0.7	4	0.5	3.5	
t_{PHZ}	DIR	A	2.1	5.4	2.2	5.4	2.2	5.5	2.2	5.4	ns
t_{PLZ}			0.9	3.8	1	3.8	0.7	3.7	0.7	3.7	
t_{PHZ}	DIR	B	4.8	20.2	2.5	9.8	1	8.5	2.5	6.5	ns
t_{PLZ}			3.2	14.8	2.5	7.4	2.5	7	1.6	4.5	
t_{PZH} (1)	DIR	A		22		12.5		11.4		8.4	ns
t_{PZL} (1)				27.2		14.4		12.5		10	
t_{PZH} (1)	DIR	B		18.9		11.3		9.1		7.6	ns
t_{PZL} (1)				17.6		11.6		10		8.6	

(1) The enable time is a calculated value, derived using the formula shown in the *セクション 9.2.2.2.1* section.

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6.10 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CCA} = V_{CCB} = 1.8 V	V_{CCA} = V_{CCB} = 2.5 V	V_{CCA} = V_{CCB} = 3.3 V	V_{CCA} = V_{CCB} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C_{pdA} (1)	A-port input, B-port output	C_L = 0 pF, f = 10 MHz, $t_r = t_f$ = 1 ns	3	4	4	4	pF
	B-port input, A-port output		18	19	20	21	
C_{pdB} (1)	A-port input, B-port output	C_L = 0 pF, f = 10 MHz, $t_r = t_f$ = 1 ns	18	19	20	21	pF
	B-port input, A-port output		3	4	4	4	

(1) Power dissipation capacitance per transceiver

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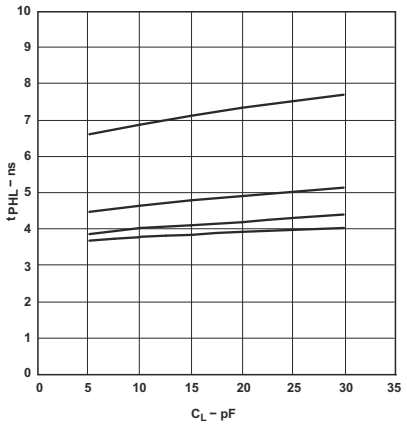
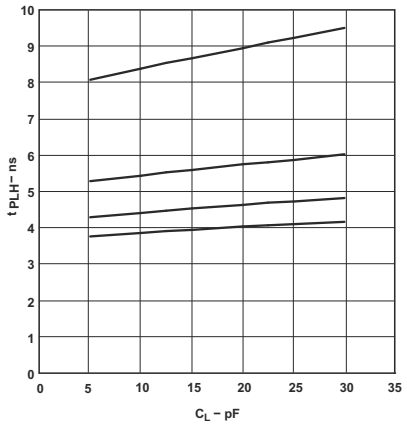
6.11 Typical Characteristics



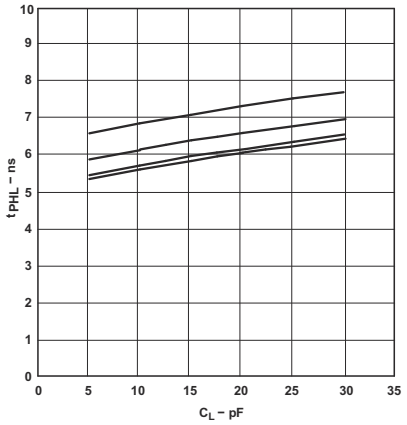
T_A = 25°C, V_{CCA} = 1.8 V

図 6-1. Typical Propagation Delay (A to B) vs Load Capacitance



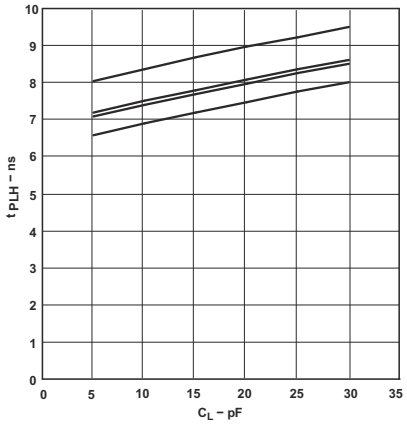
T_A = 25°C, V_{CCA} = 1.8 V

図 6-2. Typical Propagation Delay (B to A) vs Load Capacitance



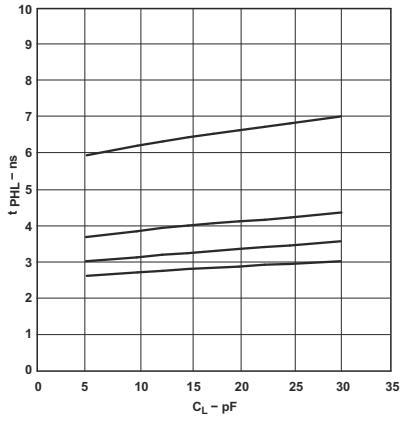
T_A = 25°C, V_{CCA} = 2.5 V

図 6-3. Typical Propagation Delay (A to B) vs Load Capacitance



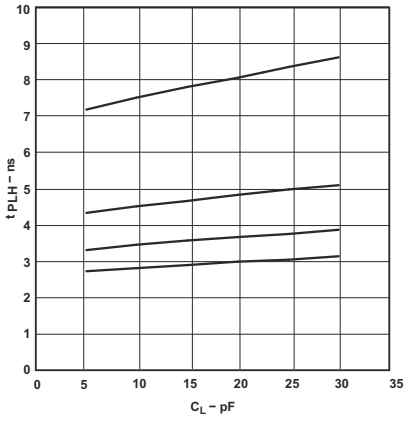
T_A = 25°C, V_{CCA} = 2.5 V

図 6-4. Typical Propagation Delay (B to A) vs Load Capacitance



T_A = 25°C, V_{CCA} = 3.3 V

図 6-5. Typical Propagation Delay (A to B) vs Load Capacitance



T_A = 25°C, V_{CCA} = 3.3 V

図 6-6. Typical Propagation Delay (B to A) vs Load Capacitance

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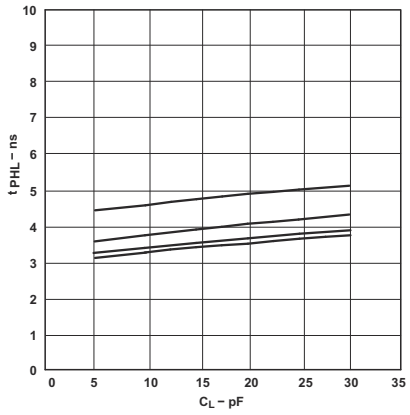
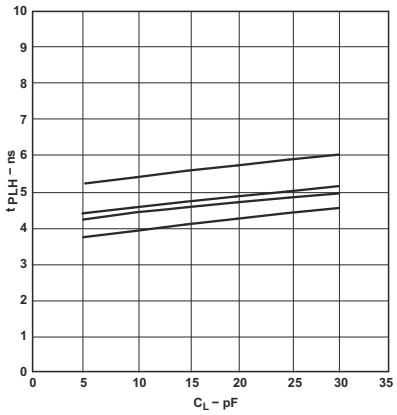
6.11 Typical Characteristics (continued)



T_A = 25°C, V_{CCA} = 5 V

図 6-7. Typical Propagation Delay (A to B) vs Load Capacitance



T_A = 25°C, V_{CCA} = 5 V

図 6-8. Typical Propagation Delay (B to A) vs Load Capacitance

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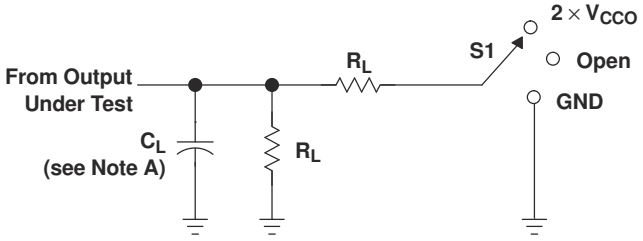
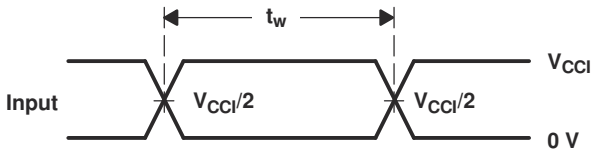
7 Parameter Measurement Information



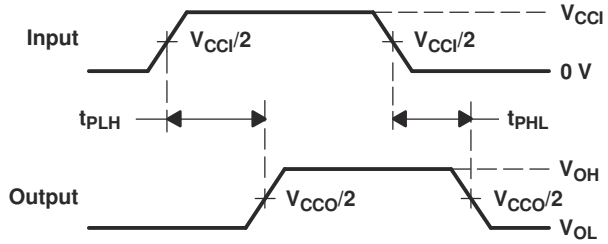
LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CCO}$
t_{PHZ}/t_{PZH}	GND

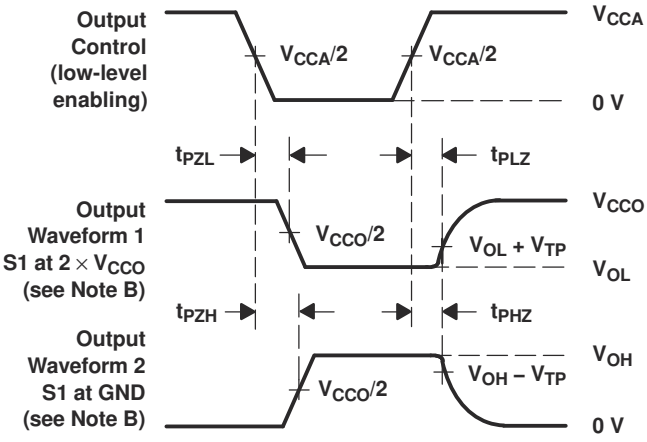
V_{CCO}	C_L	R_L	V_{TP}
1.8 V ± 0.15 V	15 pF	2 kΩ	0.15 V
2.5 V ± 0.2 V	15 pF	2 kΩ	0.15 V
3.3 V ± 0.3 V	15 pF	2 kΩ	0.3 V
5 V ± 0.5 V	15 pF	2 kΩ	0.3 V



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, dv/dt ≥ 1 V/ns.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. V_{CCI} is the V_{CC} associated with the input port.
I. V_{CCO} is the V_{CC} associated with the output port.
J. All parameters and waveforms are not applicable to all devices.

図 7-1. Load Circuit and Voltage Waveforms

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8 Detailed Description

8.1 Overview

The SN74LVC1T45 is a single-bit, dual-supply, noninverting voltage level transceiver. Pin A and the direction control pin (DIR) are supported by V_{CCA} and pin B is supported by V_{CCB}. The A port is able to accept I/O voltages ranging from 1.65 V to 5.5 V, while the B port can accept I/O voltages from 1.65 V to 5.5 V. The high on the DIR allows data transmissions from A to B and a low on the DIR allows data transmissions from B to A.

8.2 Functional Block Diagram

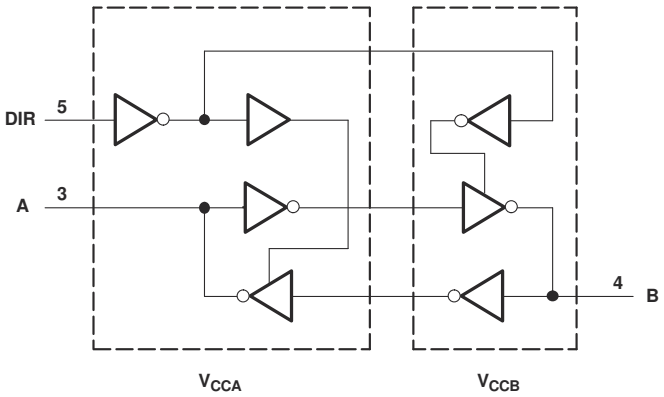

図 8-1. Logic Diagram (Positive Logic)

8.3 Feature Description

8.3.1 Fully Configurable Dual-Rail Design Allows Each Port to Operate Over the Full 1.65-V to 5.5-V Power-Supply Range

Both V_{CCA} and V_{CCB} can be supplied at any voltage between 1.65 V and 5.5 V, making the device suitable for translating between any of the voltage nodes (1.8-V, 2.5-V, 3.3-V, and 5-V).

8.3.2 Support High Speed Translation

The SN74LVC1T45 device supports high data rate applications. The translated signal data rate can be up to 420 Mbps when the signal is translated from 3.3 V to 5 V.

8.3.3 I_{off} Supports Partial Power-Down Mode Operation

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Charateristics*.

8.3.4 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so impedance matching and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. Two outputs can be connected together for a stronger output drive strength. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

8.3.5 V_{cc} Isolation

The I/O's of both ports will enter a high-impedance state when either of the supplies are at GND, while the other supply is still connected to the device. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.

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8.4 Device Functional Modes

表 8-1. Function Table(1)

INPUT DIR	OPERATION
L	B data to A bus
H	A data to B bus

(1) Input circuits of the data I/Os always are active.

9 Applications and Implementation

注

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9.1 Application Information

The SN74LVC1T45 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The maximum data rate can be up to 420 Mbps when device translates signals from 3.3 V to 5 V.

9.2 Typical Application

9.2.1 Unidirectional Logic Level-Shifting Application

図 9-1 shows an example of the SN74LVC1T45 being used in a unidirectional logic level-shifting application.

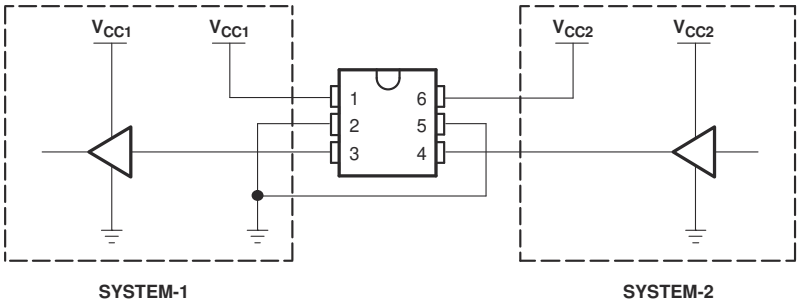

図 9-1. Unidirectional Logic Level-Shifting Application

9.2.1.1 Design Requirements

For this design example, use the parameters listed in 表 9-1.

表 9-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	1.65 V to 5.5 V
Output voltage range	1.65 V to 5.5 V

9.2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

• Input voltage range

- Use the supply voltage of the device that is driving the SN74LVC1T45 device to determine the input voltage range. For a valid logic high the value must exceed the V_{IH} of the input port. For a valid logic low the value must be less than the V_{IL} of the input port.

• Output voltage range

- Use the supply voltage of the device that the SN74LVC1T45 device is driving to determine the output voltage range.

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9.2.1.3 Application Curve

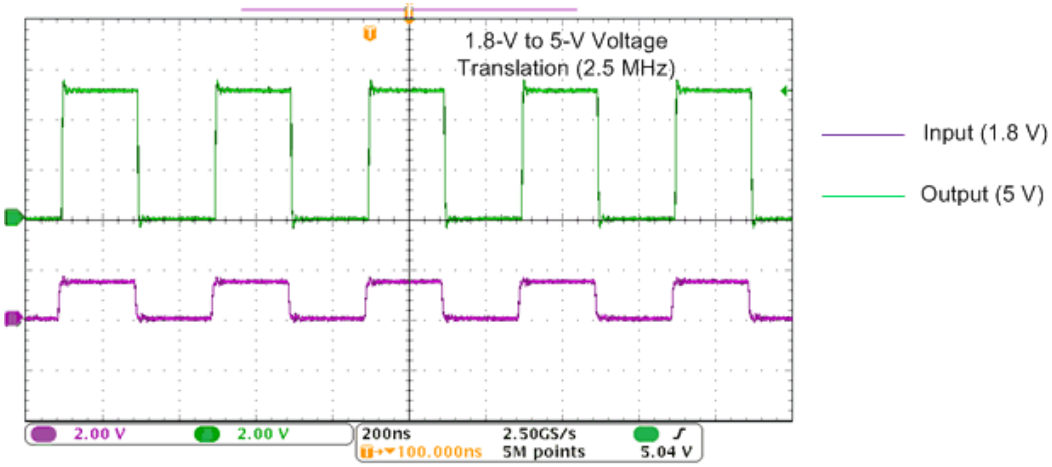

図 9-2. Translation Up (1.8 V to 5 V) at 2.5 MHz

9.2.2 Bidirectional Logic Level-Shifting Application

図 9-3 shows the SN74LVC1T45 being used in a bidirectional logic level-shifting application. Because the SN74LVC1T45 does not have an output-enable ($\overline{OE}$) pin, the system designer should take precautions to avoid bus contention between SYSTEM-1 and SYSTEM-2 when changing directions.

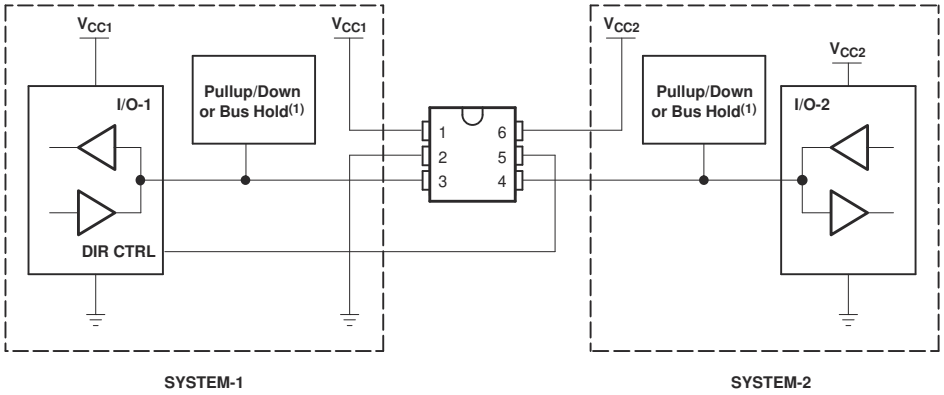

図 9-3. Bidirectional Logic Level-Shifting Application

9.2.2.1 Design Requirements

See *セクション 9.2.1.1*.

9.2.2.2 Detailed Design Procedure

表 9-2 shows data transmission from SYSTEM-1 to SYSTEM-2 and then from SYSTEM-2 to SYSTEM-1.

表 9-2. SYSTEM-1 and SYSTEM-2 Data Transmission

STATE	DIR CTRL	I/O-1	I/O-2	DESCRIPTION
1	H	Out	In	SYSTEM-1 data to SYSTEM-2
2	H	Hi-Z	Hi-Z	SYSTEM-2 is getting ready to send data to SYSTEM-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on pullup or pulldown.(1)
3	L	Hi-Z	Hi-Z	DIR bit is flipped. I/O-1 and I/O-2 still are disabled. The bus-line state depends on pullup or pulldown.(1)
4	L	In	Out	SYSTEM-2 data to SYSTEM-1

(1) SYSTEM-1 and SYSTEM-2 must use the same conditions, that is, both pullup or both pulldown.

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9.2.2.2.1 Enable Times

Calculate the enable times for the SN74LVC1T45 using the following formulas:

- t_{PZH} (DIR to A) = t_{PLZ} (DIR to B) + t_{PLH} (B to A)
- t_{PZL} (DIR to A) = t_{PHZ} (DIR to B) + t_{PHL} (B to A)
- t_{PZH} (DIR to B) = t_{PLZ} (DIR to A) + t_{PLH} (A to B)
- t_{PZL} (DIR to B) = t_{PHZ} (DIR to A) + t_{PHL} (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the SN74LVC1T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

9.2.2.3 Application Curve

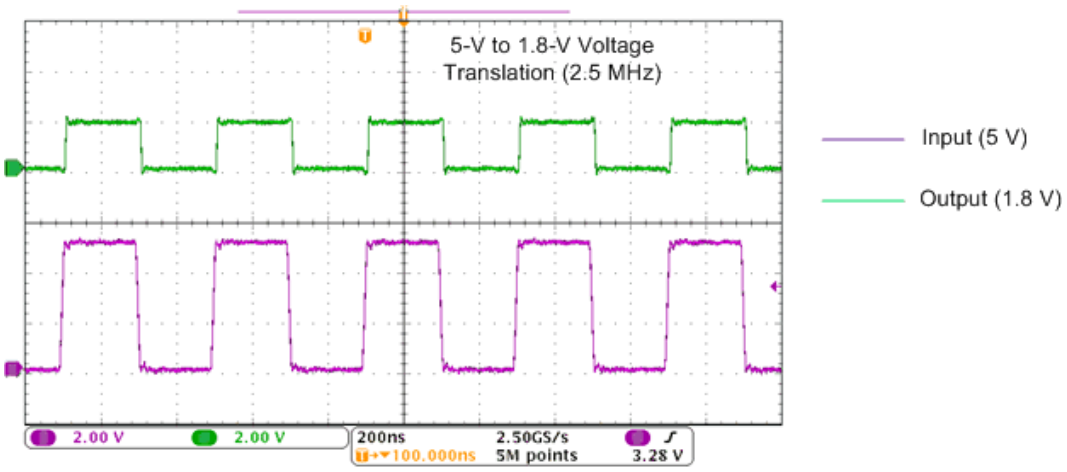

図 9-4. Translation Down (5V to 1.8 V) at 2.5 MHz

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10 Power Supply Recommendations

The SN74LVC1T45 device uses two separate configurable power-supply rails, V_{CCA} and V_{CCB}. V_{CCA} accepts any supply voltage from 1.65 V to 5.5 V and V_{CCB} accepts any supply voltage from 1.65 V to 5.5 V. The A port and B port are designed to track V_{CCA} and V_{CCB}, respectively allowing for low-voltage bidirectional translation between any of the 1.8-V, 2.5-V, 3.3-V and 5-V voltage nodes. The recommendation is to first power-up the input supply rail to help avoid internal floating while the output supply rail ramps up. However, both power-supply rails can be ramped up simultaneously.

11 Layout

11.1 Layout Guidelines

To ensure reliability of the device, the following common printed-circuit board layout guidelines are recommended:

- Bypass capacitors should be used on power supplies.
- Short trace lengths should be used to avoid excessive loading.
- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depends on the system requirements

11.2 Layout Example

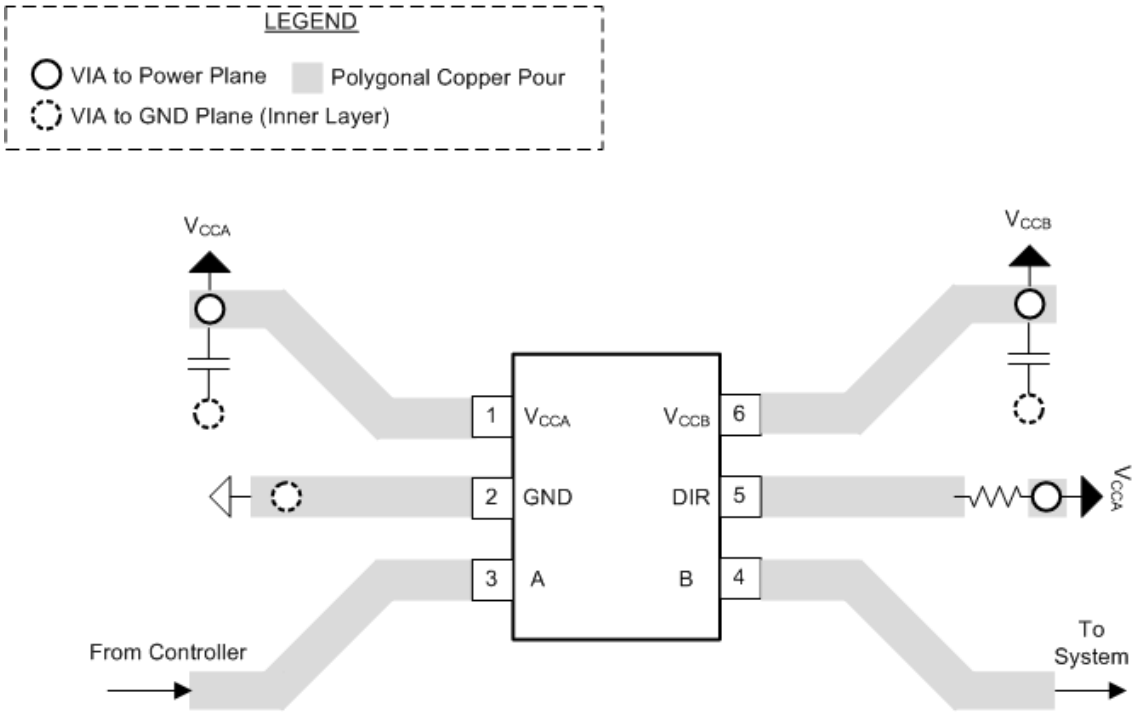

図 11-1. Layout Example

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *Implications of Slow or Floating CMOS Inputs*

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 サポート・リソース

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12.4 Trademarks

NanoFree™ is a trademark of Texas Instruments.
TI E2E™ is a trademark of Texas Instruments.
すべての商標は、それぞれの所有者に帰属します。

12.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1T45DBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(2PUH, CT15, CT1F, CT1R)	Samples
SN74LVC1T45DBVRE4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(2PUH, CT15, CT1F, CT1R)	Samples
SN74LVC1T45DBVRG4	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(2PUH, CT15, CT1F, CT1R)	Samples
SN74LVC1T45DBVT	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(CT15, CT1F, CT1R)	Samples
SN74LVC1T45DBVTG4	ACTIVE	SOT-23	DBV	6	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(CT15, CT1F, CT1R)	Samples
SN74LVC1T45DCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	(TA5, TAF, TAR)	Samples
SN74LVC1T45DCKRE4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	(TA5, TAF, TAR)	Samples
SN74LVC1T45DCKRG4	ACTIVE	SC70	DCK	6	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	(TA5, TAF, TAR)	Samples
SN74LVC1T45DCKT	ACTIVE	SC70	DCK	6	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	(TA5, TAF, TAR)	Samples
SN74LVC1T45DCKTE4	ACTIVE	SC70	DCK	6	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	(TA5, TAF, TAR)	Samples
SN74LVC1T45DCKTG4	ACTIVE	SC70	DCK	6	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	(TA5, TAF, TAR)	Samples
SN74LVC1T45DPKR	ACTIVE	USON	DPK	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TA7	Samples
SN74LVC1T45DRLR	ACTIVE	SOT-5X3	DRL	6	4000	RoHS & Green	NIPDAU | NIPDAUAG	Level-1-260C-UNLIM	-40 to 85	(1JX, TA7, TAR)	Samples
SN74LVC1T45DRLRG4	ACTIVE	SOT-5X3	DRL	6	4000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(1JX, TA7, TAR)	Samples
SN74LVC1T45YZPR	ACTIVE	DSBGA	YZP	6	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(TA2, TA7, TAN)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1T45 :

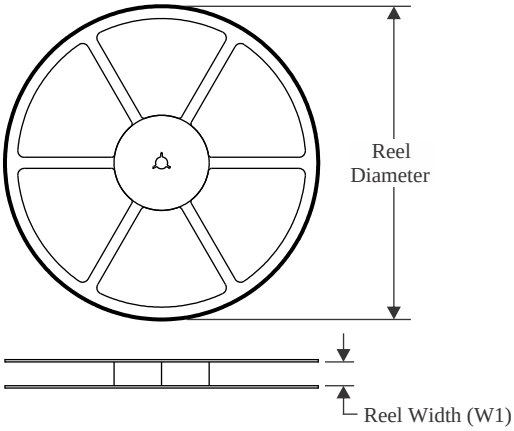
- Automotive : SN74LVC1T45-Q1
- Enhanced Product : SN74LVC1T45-EP

NOTE: Qualified Version Definitions:

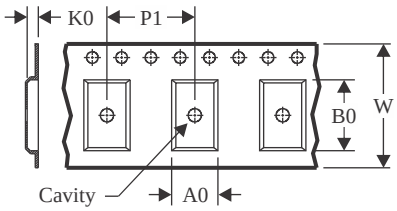
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

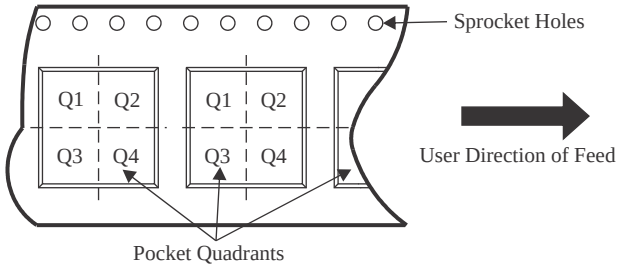


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

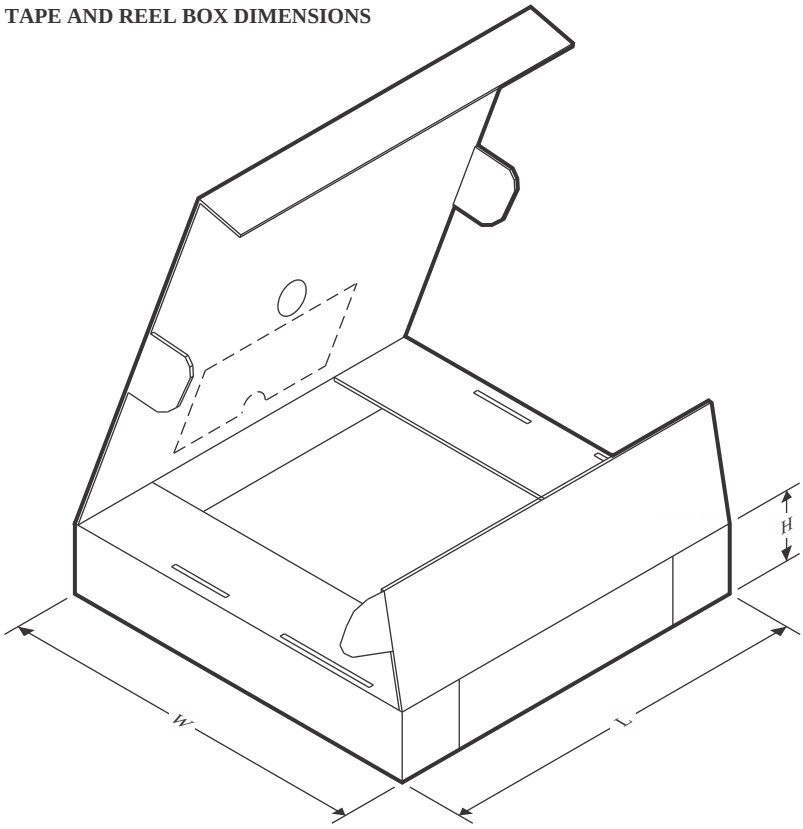
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1T45DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1T45DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1T45DBVT	SOT-23	DBV	6	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1T45DCKR	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1T45DPKR	USON	DPK	6	5000	180.0	9.5	1.75	1.75	0.7	4.0	8.0	Q2
SN74LVC1T45DRLR	SOT-5X3	DRL	6	4000	180.0	8.4	2.0	1.8	0.75	4.0	8.0	Q3
SN74LVC1T45YZPR	DSBGA	YZP	6	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

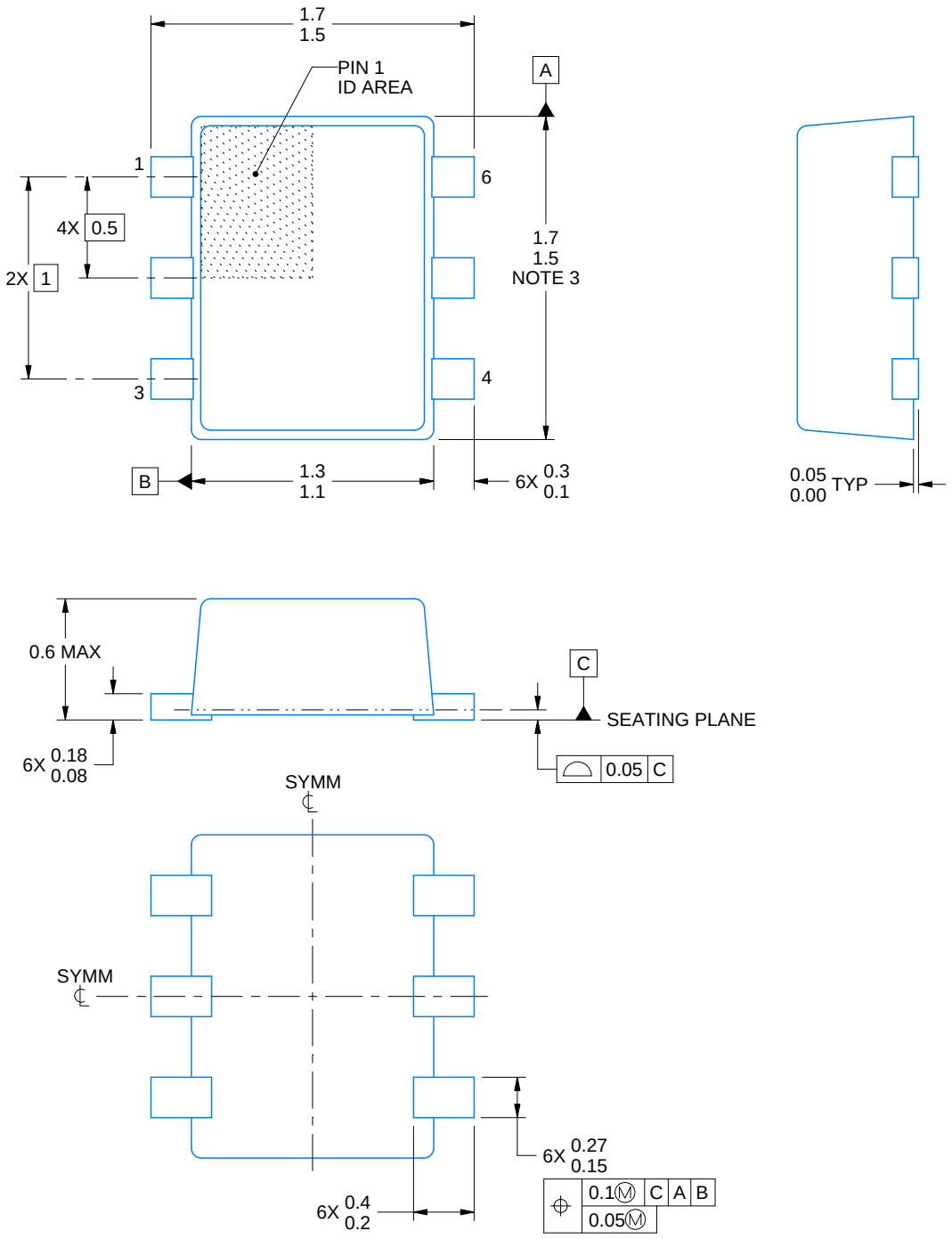
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1T45DBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
SN74LVC1T45DBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
SN74LVC1T45DBVT	SOT-23	DBV	6	250	210.0	185.0	35.0
SN74LVC1T45DCKR	SC70	DCK	6	3000	180.0	180.0	18.0
SN74LVC1T45DPKR	USON	DPK	6	5000	184.0	184.0	19.0
SN74LVC1T45DRLR	SOT-5X3	DRL	6	4000	210.0	185.0	35.0
SN74LVC1T45YZPR	DSBGA	YZP	6	3000	220.0	220.0	35.0

PACKAGE OUTLINE

DRL0006A

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



NOTES:

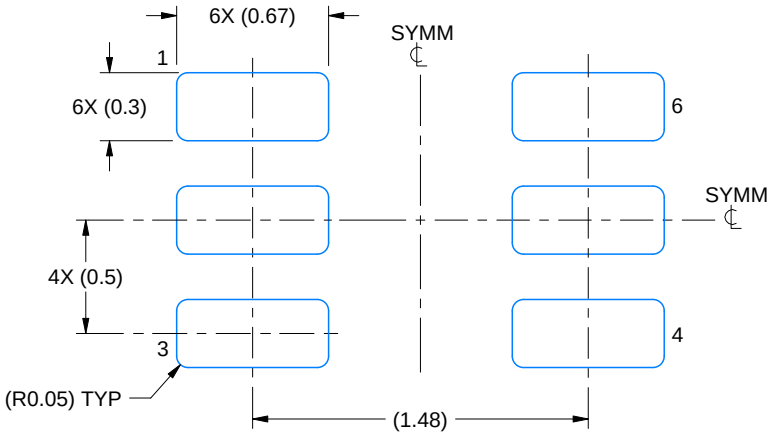
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-293 Variation UAAD

EXAMPLE BOARD LAYOUT

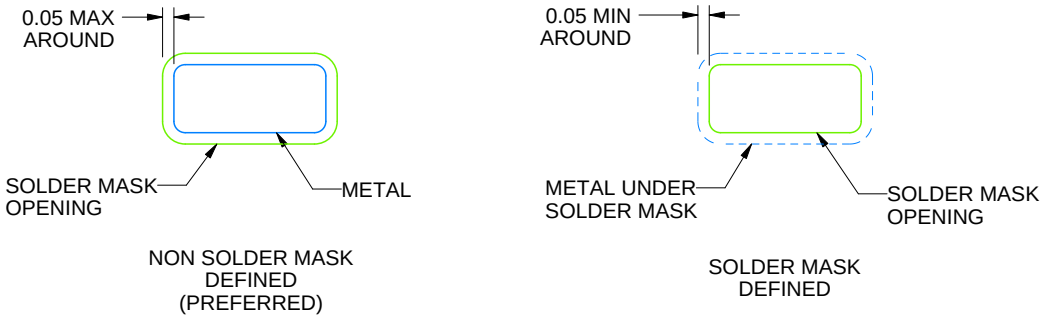
DRL0006A

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE
SCALE:30X



SOLDERMASK DETAILS

4223266/C 12/2021

NOTES: (continued)

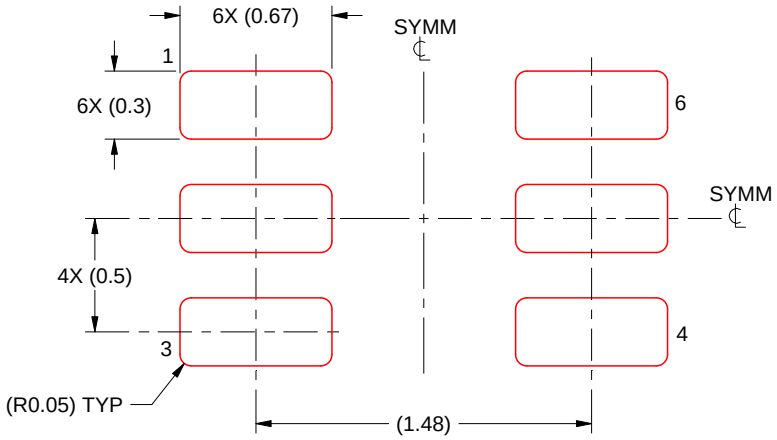
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
7. Land pattern design aligns to IPC-610, Bottom Termination Component (BTC) solder joint inspection criteria.

EXAMPLE STENCIL DESIGN

DRL0006A

SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

4223266/C 12/2021

NOTES: (continued)

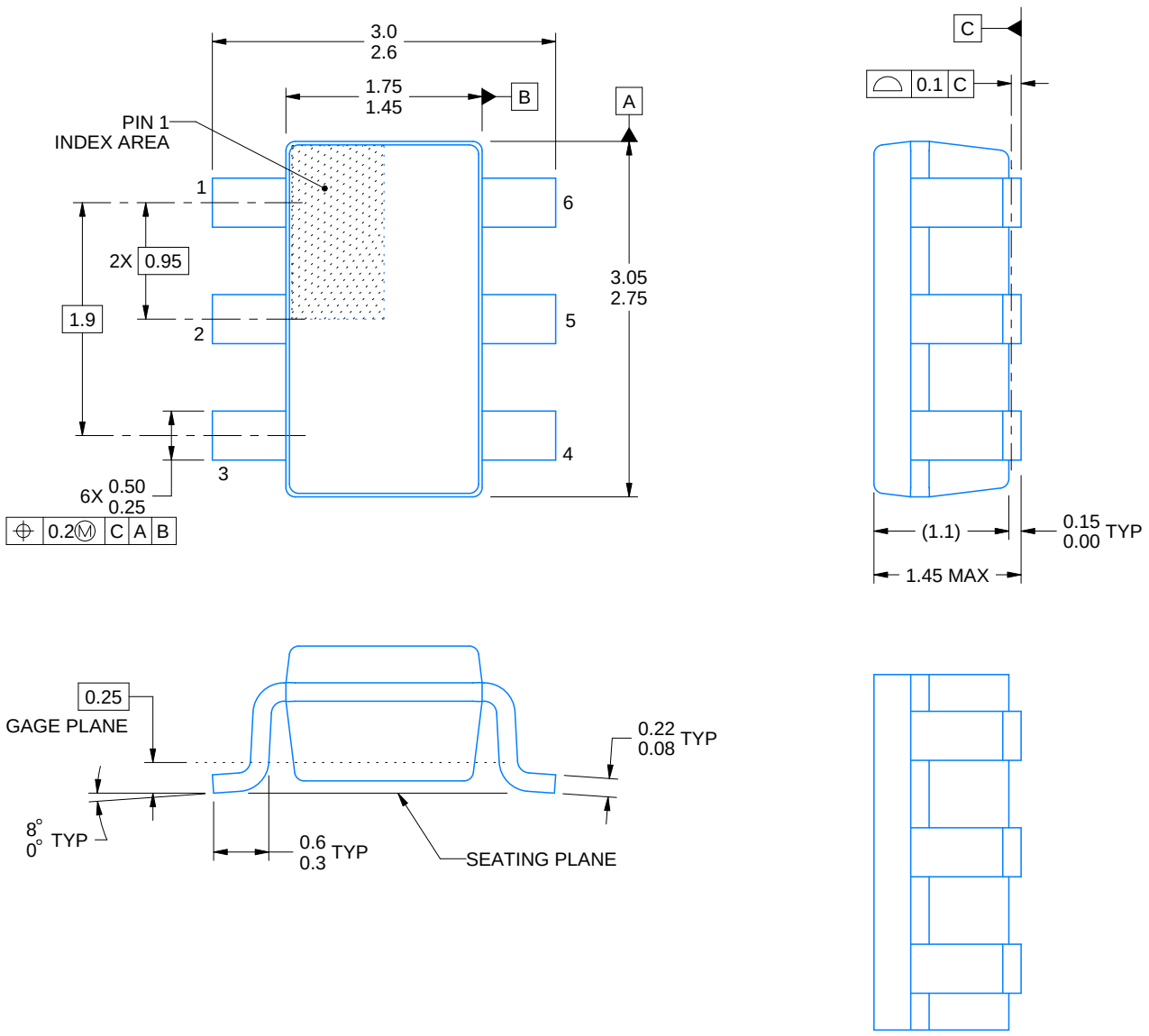
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR

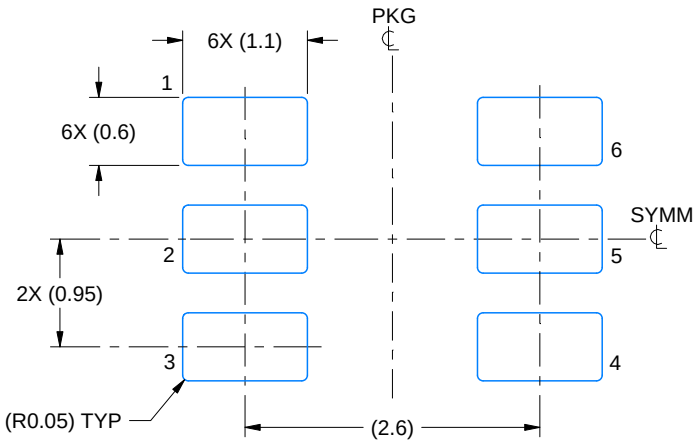


ALTERNATIVE PACKAGE SINGULATION VIEW

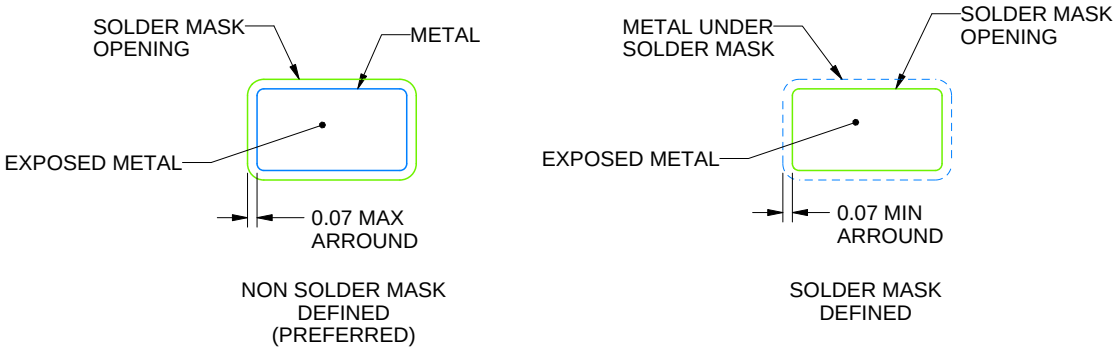
4214840/E 02/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
5. Refernce JEDEC MO-178.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

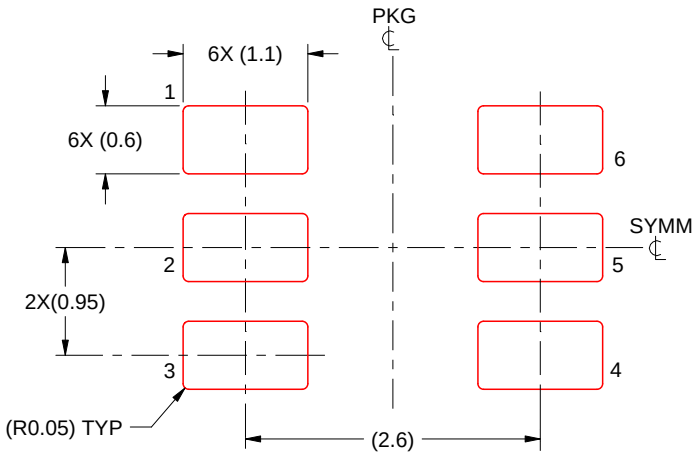


SOLDER MASK DETAILS

4214840/E 02/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



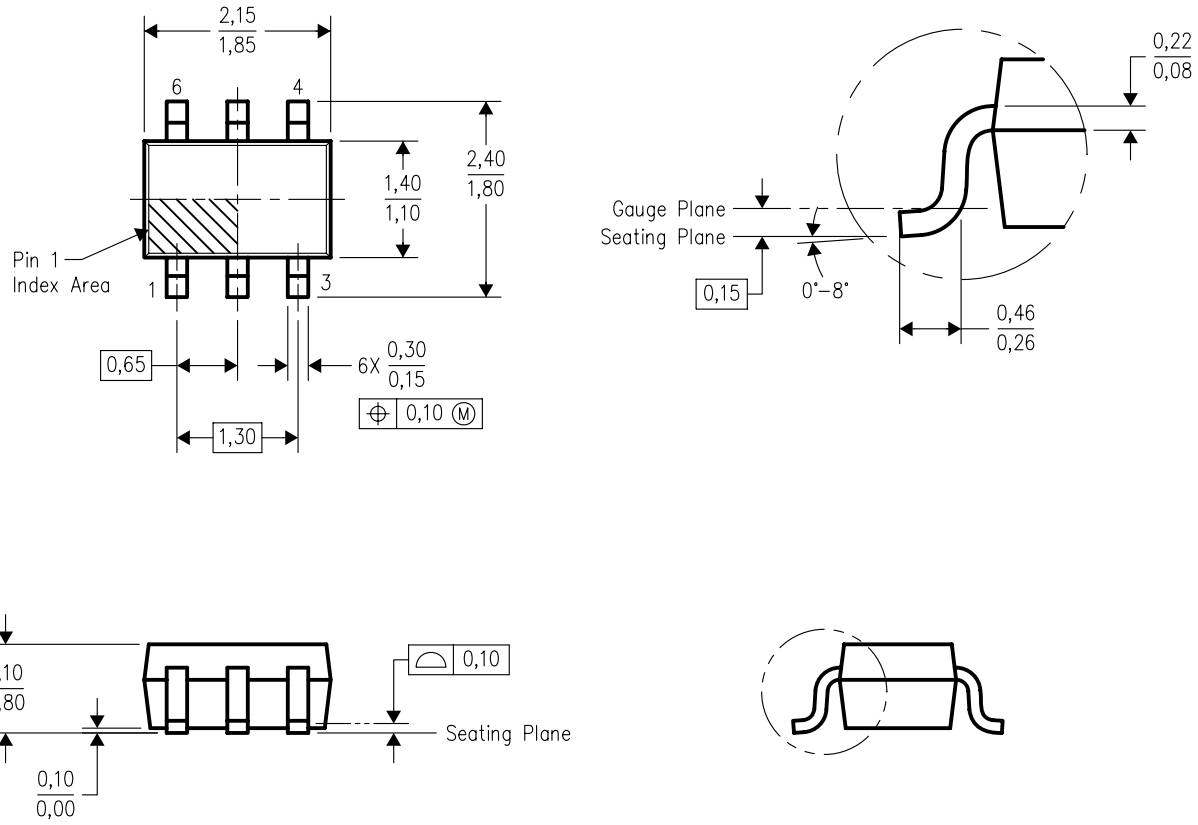
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214840/E 02/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

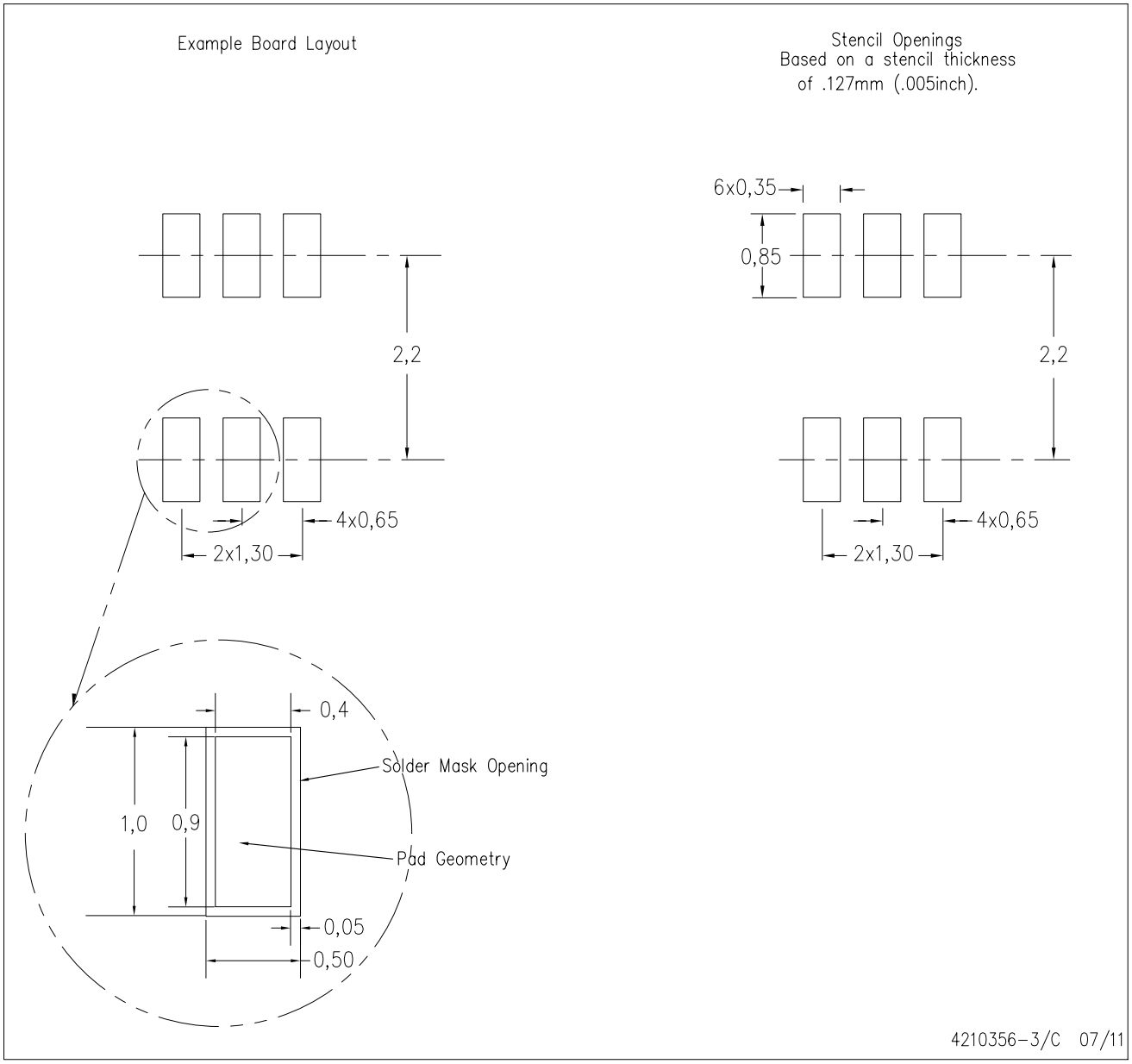
DCK (R–PDSO–G6) PLASTIC SMALL–OUTLINE PACKAGE



4093553–4/G 01/2007

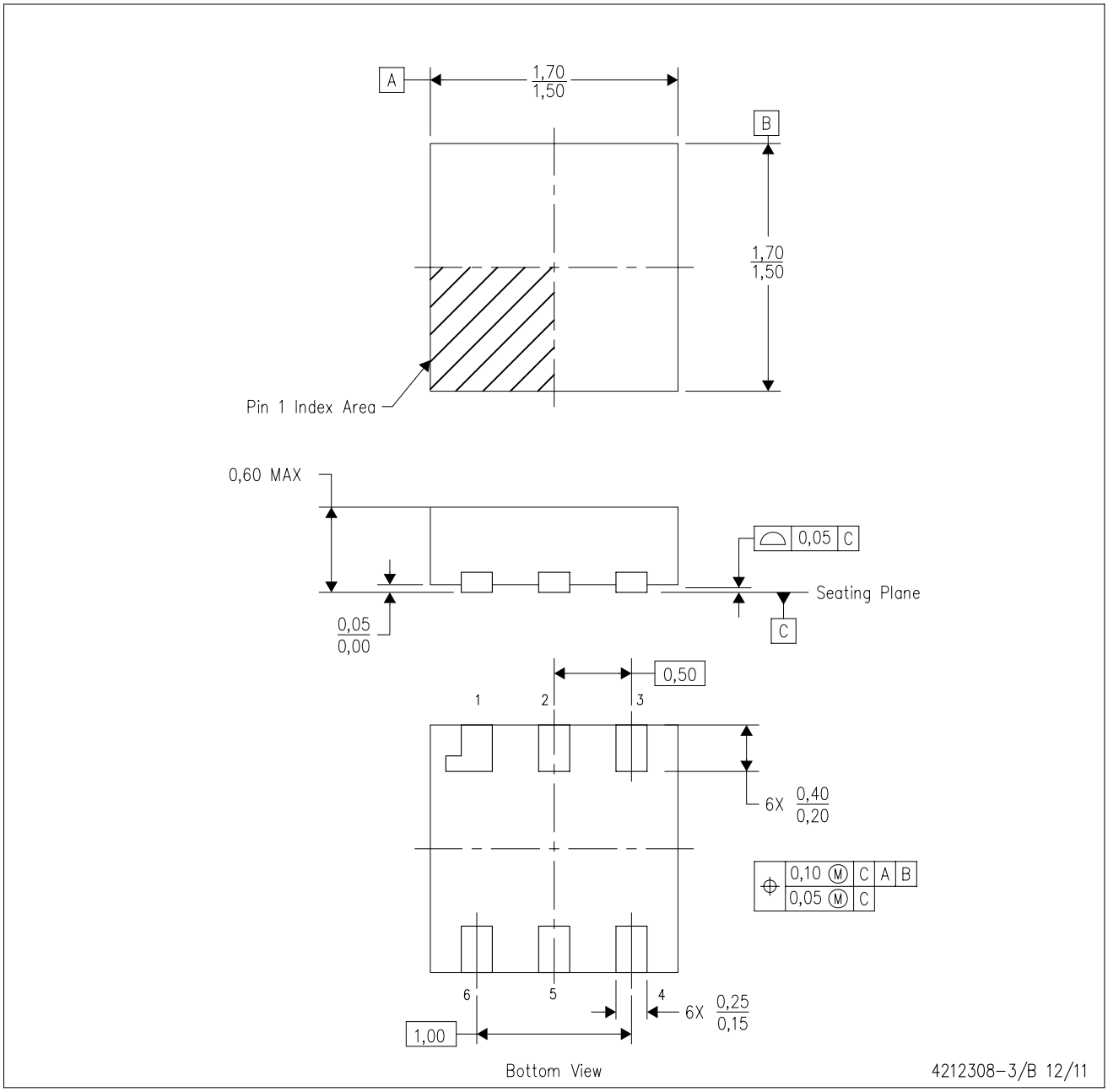
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–203 variation AB.

DCK (R–PDSO–G6) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.

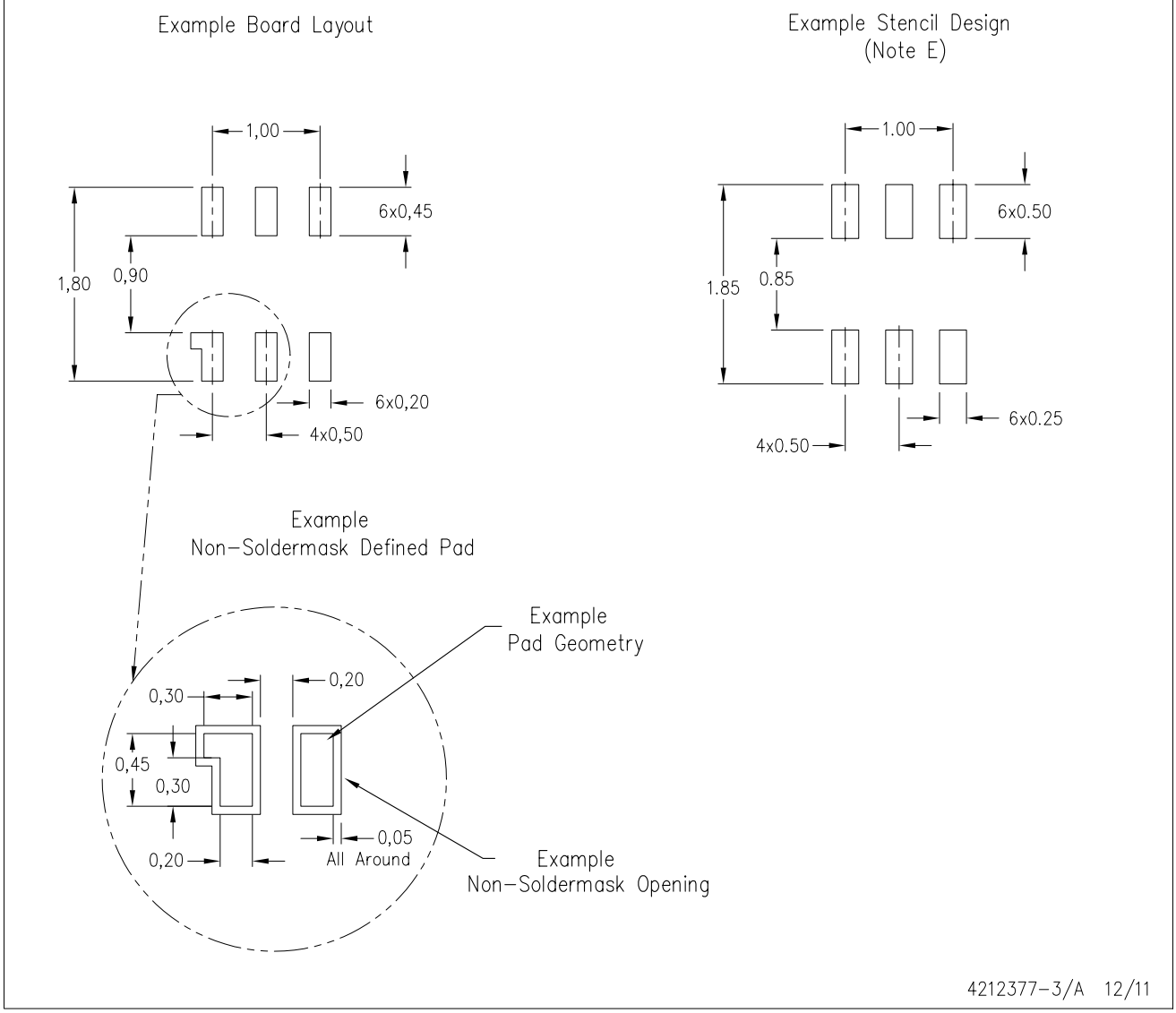
DPK (S–PUSON–N6) PLASTIC SMALL OUTLINE NO–LEAD



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.

DPK (S–PUSON–N6)

PLASTIC SMALL OUTLINE NO–LEAD



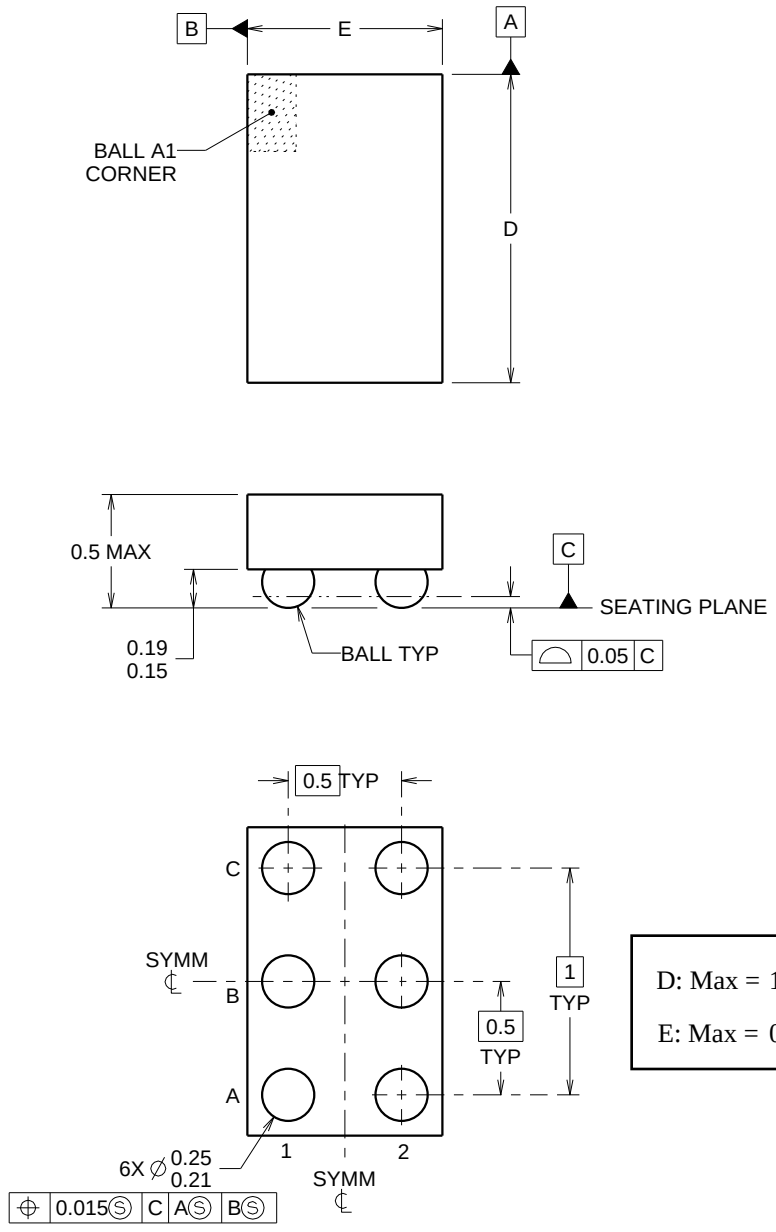
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
G. Side aperture dimensions over–print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.

PACKAGE OUTLINE

YZP0006

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



D: Max = 1.418 mm, Min =1.358 mm

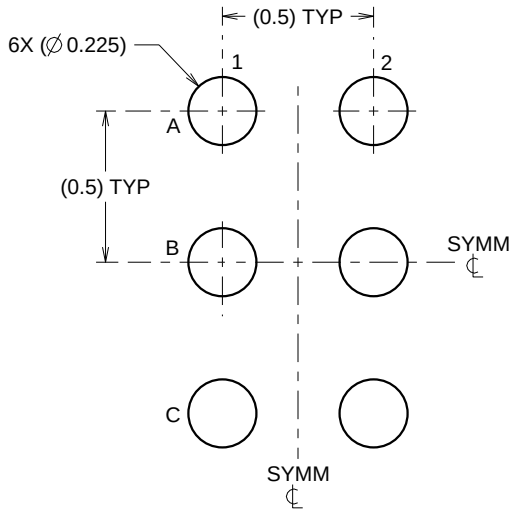
E: Max = 0.918 mm, Min =0.858 mm

4219524/A 06/2014

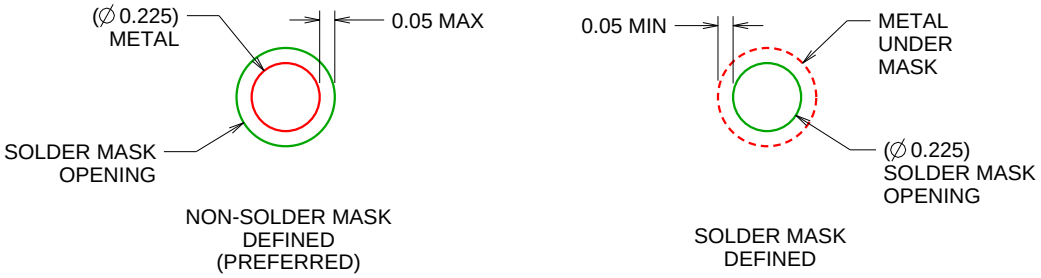
NOTES:

NanoFree Is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. NanoFree™ package configuration.



LAND PATTERN EXAMPLE
SCALE:40X



SOLDER MASK DETAILS
NOT TO SCALE

4219524/A 06/2014

NOTES: (continued)

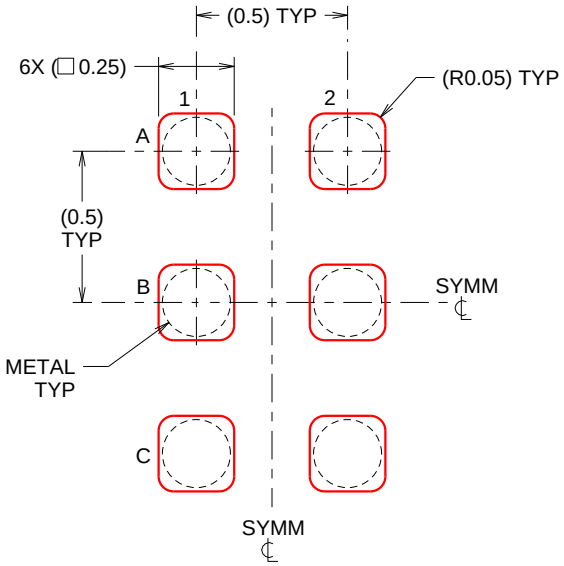
4. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).

EXAMPLE STENCIL DESIGN

YZP0006

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4219524/A 06/2014

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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